

February 16, 2012

Product Specifications of the P-Channel Power MOSFETs

Product	Drain-to-Source voltage (VDSS) (V)	Gate-to-Source voltage (VGSS) (V)	Drain current (ID) (A)	On-resistance (mΩ)				Input capacitance (Ciss) (pF)	Package
				VGSS = 10 V		VGSS = 4.5 V			
				Typ	Max	Typ	Max		
μPA2812T1L	-30	±20	30	4.2	5.2	6.9	9.9	3850	HVSON(3333) <3.3 × 3.3 mm ² >
μPA2813T1L	-30	±20	27	5.6	7	9	13	3160	
μPA2814T1S	-30	±20	24	7.2	9	12	17	2810	
μPA2815T1S	-30	±20	21	9	12	16	23	1760	
μPA2816T1S	-30	±20	17	12	18	28	45	1210	